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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HD74HC595

8-bit Shift Register/Latch (with 3-state outputs)

ADE-205-514 (Z)
1st. Edition
Sep. 2000

Description

This device each contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. The storage register has parallel 3-state outputs. Separate clocks are provided for both the shift register and the storage register. The shift register has a direct-overriding clear, serial input, and serial output pins for cascading.

Both the shift register and storage register clocks are positive-edge triggered. If the user wishes to connect both clocks together, the shift register state will always be one clock pulse ahead of the storage register.

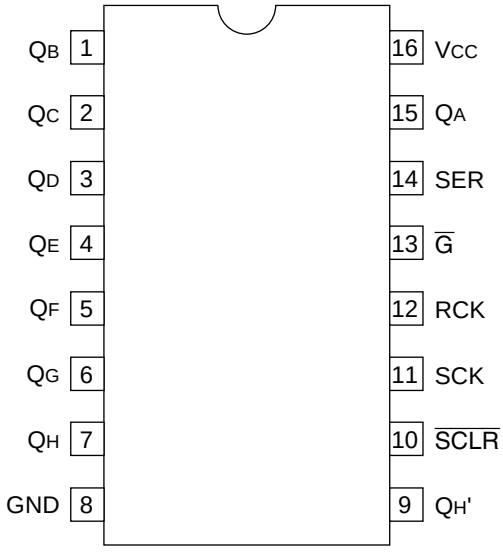
Features

- High Speed Operation: t_{pd} (RCK to Q) = 17 ns typ (C_L = 50 pF)
- High Output Current: Fanout of 15 LSTTL Loads (Q_A to Q_H outputs)
- Wide Operating Voltage: V_{CC} = 2 to 6 V
- Low Input Current: 1 μA max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μA max (Ta = 25°C)

Function Table

RCK	SCK	$\overline{\text{SCLR}}$	$\overline{\text{G}}$	Function
X	X	X	H	Q_A to Q_H high impedance
X	X	L	X	Shift register cleared Q_H' = L
X	⎍	H	X	Shift register clocked $Q_n = Q_{n-1}$, Q_A = SER
⎍	X	H	X	Contents of shift register transferred to output latches

Pin Arrangement

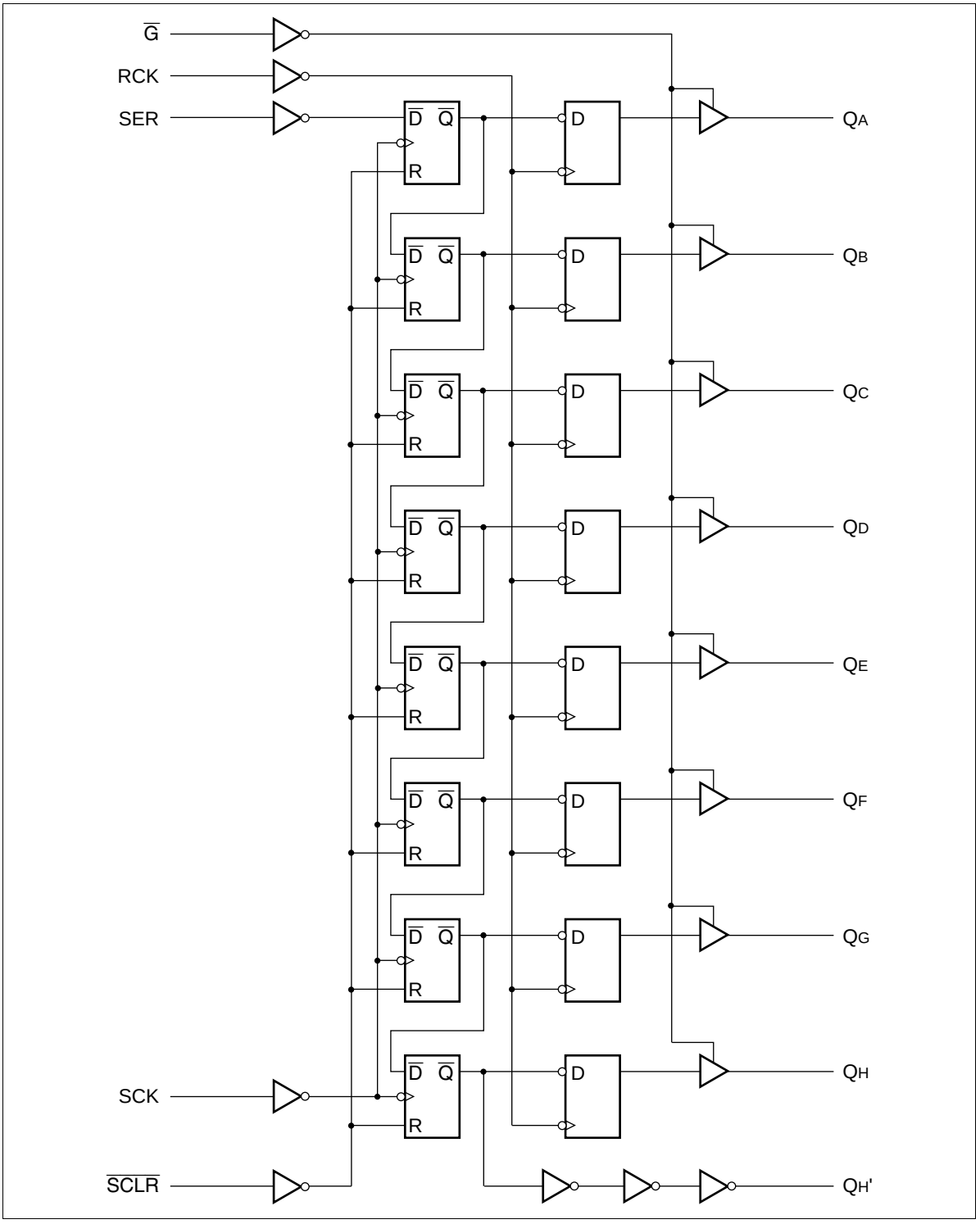


(Top view)

Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	–0.5 to +7.0	V
Input voltage	V_{IN}	–0.5 to V_{CC} + 0.5	V
Output voltage	V_{OUT}	–0.5 to V_{CC} + 0.5	V
Output current	I_{OUT}	±35	mA
DC current drain per V_{CC}, GND	I_{CC}, I_{GND}	±75	mA
DC input diode current	I_{IK}	±20	mA
DC output diode current	I_{OK}	±20	mA
Power dissipation per package	P_T	500	mW
Storage Temperature	Tstg	–65 to +150	°C

Logic Diagram



DC Characteristics

Item	Symbol	V_{CC} (V)	Ta = 25°C Min	Typ	Max	Ta = –40 to +85°C Min	Max	Unit	Test Conditions	
Input voltage	V_{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V_{IL}	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V_{OH}	2.0	1.9	2.0	—	1.9	—	V	Q_A to Q_H	I_{OH} = –20 µA
		4.5	4.4	4.5	—	4.4	—		Vin = V_{IH} or V_{IL}	
		6.0	5.9	6.0	—	5.9	—			
		4.5	4.18	—	—	4.13	—			I_{OH} = –6 mA
		6.0	5.68	—	—	5.63	—			I_{OH} = –7.8 mA
	V_{OL}	2.0	—	0.0	0.1	—	0.1	V	Q_A to Q_H	I_{OL} = 20 µA
		4.5	—	0.0	0.1	—	0.1		Vin = V_{IH} or V_{IL}	
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			I_{OL} = 6 mA
		6.0	—	—	0.26	—	0.33			I_{OL} = 7.8 mA
Output voltage	V_{OH}	2.0	1.9	2.0	—	1.9	—	V	Q'_H	I_{OH} = –20 µA
		4.5	4.4	4.5	—	4.4	—		Vin = V_{IH} or V_{IL}	
		6.0	5.9	6.0	—	5.9	—			
		4.5	4.18	—	—	4.13	—			I_{OH} = –4 mA
		6.0	5.68	—	—	5.63	—			I_{OH} = –5.2 mA
	V_{OL}	2.0	—	0.0	0.1	—	0.1	V	Q'_H	I_{OL} = 20 µA
		4.5	—	0.0	0.1	—	0.1		Vin = V_{IH} or V_{IL}	
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			I_{OL} = 4 mA
		6.0	—	—	0.26	—	0.33			I_{OL} = 5.2 mA
Off-state output current	I_{OZ}	6.0	—	—	±0.5	—	±5.0	µA	Vin = V_{IH} or V_{IL}, Vout = V_{CC} or GND	
Input current	Iin	6.0	—	—	±0.1	—	±1.0	µA	Vin = V_{CC} or GND	
Quiescent supply current	I_{CC}	6.0	—	—	4.0	—	40	µA	Vin = V_{CC} or GND, Iout = 0 µA	

AC Characteristics (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

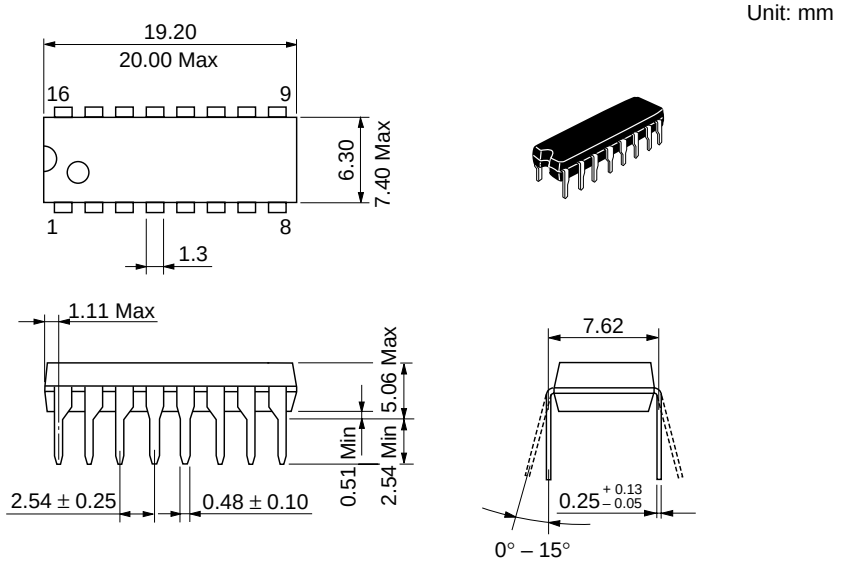
			Ta = 25°C			Ta = –40 to +85°C			
Item	**Symbol**	**V_{cc} (V)**	**Min**	**Typ**	**Max**	**Min**	**Max**	**Unit**	**Test Conditions**
Maximum clock frequency	f_{max}	2.0	—	—	5	—	4	MHz	
		4.5	—	—	27	—	21		
		6.0	—	—	31	—	24		
Propagation delay time	t_{PLH} t_{PHL}	2.0	—	—	115	—	145	ns	SCK to Q_H'
		4.5	—	12	23	—	29		
		6.0	—	—	20	—	25		
	t_{PLH} t_{PHL}	2.0	—	—	150	—	190	ns	RCK to Q
		4.5	—	17	30	—	38		
		6.0	—	—	26	—	33		
	t_{PLH}	2.0	—	—	175	—	220	ns	$\overline{SCLR}$ to Q_H'
		4.5	—	20	35	—	44		
		6.0	—	—	30	—	37		
Output enable time	t_{ZL} t_{ZH}	2.0	—	—	150	—	190	ns	
		4.5	—	13	30	—	38		
		6.0	—	—	26	—	33		
Output disable time	t_{LZ} t_{HZ}	2.0	—	—	150	—	190	ns	
		4.5	—	15	30	—	38		
		6.0	—	—	26	—	33		
Setup time	t_{su}	2.0	100	—	—	125	—	ns	SER to SCK
		4.5	20	1	—	25	—		
		6.0	17	—	—	21	—		
		2.0	200	—	—	250	—	ns	SCK to RCK
		4.5	40	8	—	50	—		
		6.0	34	—	—	43	—		
Pulse width	t_w	2.0	80	—	—	100	—	ns	
		4.5	16	8	—	20	—		
		6.0	14	—	—	17	—		
Removal time	t_{rem}	2.0	100	—	—	125	—	ns	
		4.5	20	—	—	25	—		
		6.0	17	—	—	21	—		

AC Characteristics (C_L = 50 pF, Input t_r = t_f = 6 ns) (cont)

			Ta = 25°C			Ta = –40 to +85°C			
Item	**Symbol**	**V_{cc} (V)**	**Min**	**Typ**	**Max**	**Min**	**Max**	**Unit**	**Test Conditions**
Hold time	t_h	2.0	5	—	—	5	—	ns	
		4.5	5	1	—	5	—		
		6.0	5	—	—	5	—		
Output rise/fall time	t_{TLH}	2.0	—	—	75	—	95	ns	Q_H'
	t_{THL}	4.5	—	5	15	—	19		
		6.0	—	—	13	—	16		
		2.0	—	—	60	—	75	ns	Q
		4.5	—	4	12	—	15		
		6.0	—	—	10	—	13		
Input capacitance	Cin	—	—	5	10	—	5	pF	

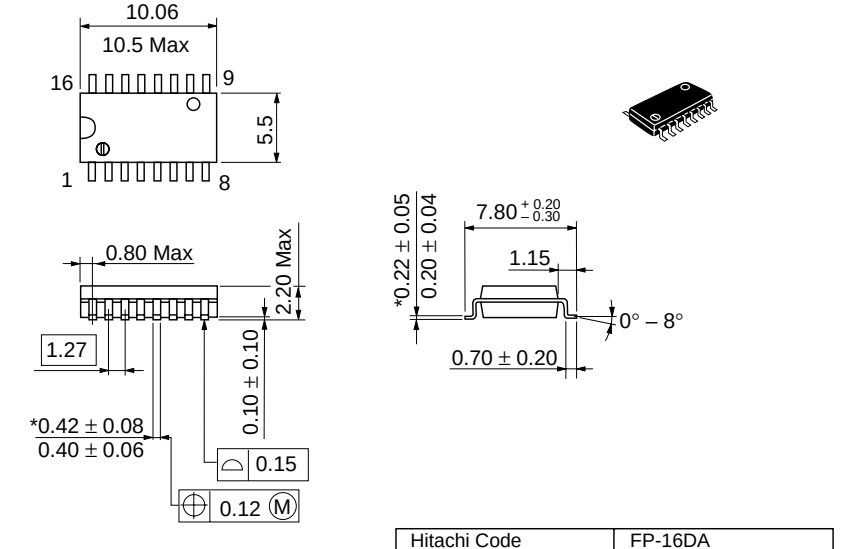
Package Dimensions

Unit: mm



Hitachi Code	DP-16
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	1.07 g

Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DA
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.24 g

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HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : http://semiconductor.hitachi.com/
Europe : http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor (America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straβe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel : <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : http://www.hitachi.com.sg

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel : <852>-(2)-735-9218
Fax : <852>-(2)-730-0281
URL : http://www.hitachi.com.hk

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